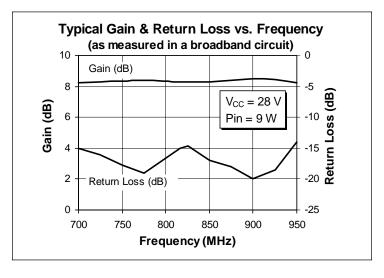


PTB 20155 9 Watts, 610–960 MHz UHF Power Transistor

Description

The 20155 is an NPN common base RF power transistor intended for 28 Vdc class C operation from 610 to 960 MHz. Rated at 9 watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.

- 9 Watts, 610-960 MHz
- · Class C Characteristics
- Gold Metallization
- Silicon Nitride Passivated





Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CER}	40	Vdc
Collector-Base Voltage	V _{CBO}	50	Vdc
Emitter-Base Voltage (collector open)	V _{EBO}	4	Vdc
Collector Current (continuous)	Ic	6.7	Adc
Total Device Dissipation at T _{flange} = 25°C Above 25°C derate by	P _D	65 0.37	Watts W/°C
Storage Temperature Range	T _{STG}	-40 to +150	°C
Thermal Resistance (Tflange = 70°C)	$R_{ heta JC}$	2.7	°C/W

PTB 20155



Electrical Characteristics (100% Tested)

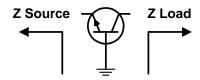
Characteristic	Conditions	Symbol	Min	Тур	Max	Units
Breakdown Voltage C to E	$V_{BE} = 0 \text{ V, } I_{C} = 5 \text{ mA}$	V _{(BR)CES}	50	_	_	Volts
Breakdown Voltage E to B	I _C = 0 A, I _E = 5 mA	V _{(BR)EBO}	3.5	_	_	Volts
DC Current Gain	V _{CE} = 5 V, I _C = 300 mA	h _{FE}	25	_	100	_
Output Capacitance	V _{CB} = 28 V, I _E = 0 A, f = 1 MHz	C _{ob}	_	10.5	11	pF
Collector Cut-off Current	V _{CB} = 28 V, I _E = 0 A	I _{CBO}	_	_	1.5	mA

RF Specifications (100% Tested)

Characteristic		Min	Тур	Max	Units
Gain					
(V _{CC} = 28 Vdc, P _{out} = 9 W, f = 960 MHz)	G _{pe}	8.0	9.0	_	dB
Collector Efficiency					
(V _{CC} = 28 Vdc, P _{out} = 9 W, f = 960 MHz)		45	53	_	%

Impedance Data (data shown for fixed-tuned broadband circuit)

 $(V_{CC} = 28 \text{ Vdc}, P_{out} = 9 \text{ W})$



Frequency	Z Source		equency Z Source		Z L	oad
MHz	R	jХ	R	jX		
850	4.4	-10.7	8.6	3.6		
900	6.4	-10.0	9.3	4.9		
960	6.4	-14.3	7.8	3.1		





